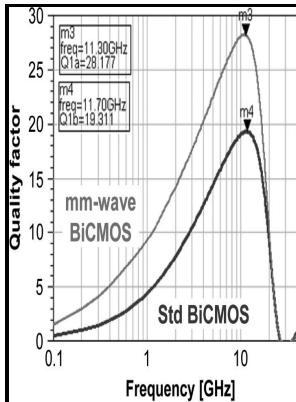


# Fabrication of SiGe HBT BiCMOS technology

CRC Press - Fabrication Of Sige Hbt Bicmos Technology



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. Access to high-performance SiGe technology has spurred a rich diversity of exploratory and commercial circuit applications, many elaborated in this text. I hope our efforts please you.

**Dr. John D. Cressler**

. Scaling of lateral device dimensions is essential for simultaneous realization of low  $R_B$  and low  $C_{BC}$  that is required for high  $f_{MAX}$  values. Growth of inverse tetragonal distorted SiGe layer on Si 0 0 1 by adding small amounts of carbon.

**High**

. D Khang and MM Atalla.

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An additional reduction of  $R_B$  was achieved by optimizing the process for the selective epitaxial growth and by increasing the dopant concentration of the elevated external base regions. . As depicted in Figure 1.

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A novel aspect of this book the inclusion of numerous snapshot views of the industrial state-of-the-art for SiGe HBT BiCMOS technology. A Fischer, H-J Osten, and H Richter.

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The typical transistor characteristics of a SiGe HBT with an emitter area of 0. Technical Digest of the IEEE International Electron Devices Meeting, Washington, 1990, pp. B Rejaei, JL Tauritz, and P Snoeij.

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